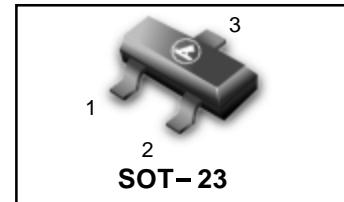


# SCHOTTKY BARRIER (DOUBLE) DIODE

**LBAS40\*LT1**



## Features

- Low forward current
- Guard ring protected
- Low diode capacitance.

## APPLICATIONS

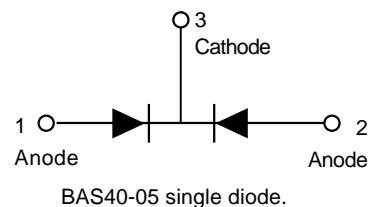
- Ultra high-speed switching
- Voltage clamping
- Protection circuits.
- Blocking diodes.

## DESCRIPTION

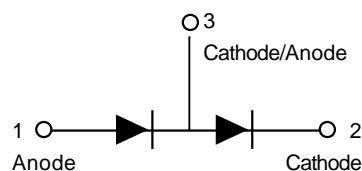
Planar Schottky barrier diodes with an integrated guard ring for stress protection.



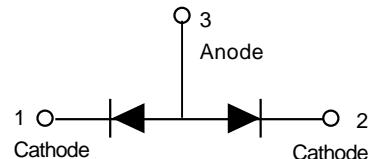
BAS40 single diode.



BAS40-05 single diode.



BAS40-04 single diode.



BAS40-06 single diode.

**LBAS40 Series**
**MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

Parameter	Symbol	Min.	Max.	Unit	Conditions
Continuous reverse voltage	V <sub>R</sub>	–	40	V	
Continuous forward current	I <sub>F</sub>	–	120	mA	
Repetitive Peak forward surge current	I <sub>FSM</sub>	–	120	mA	t <sub>p</sub> ≤1s;δ≤0.5
Non-repetitive peak forward current	I <sub>FSM</sub>	–	200	mA	t <sub>p</sub> <10ms
Storage temperature	T <sub>stg</sub>	-65	+150	°C	
Junction temperature	T <sub>j</sub>	–	150	°C	
Operating ambient temperature	T <sub>amb</sub>	-65	+150	°C	

**DEVICE MARKING**

LBAS40LT1=B1 LBAS40-04LT1=CB LBAS40-05LT1=45 LBAS40-06LT1=L2

**ELECTRICAL CHARACTERISTICS(T<sub>A</sub>=25°C)**

Parameter	Symbol	Max.	Unit	Conditions
Forward voltage(Fig.1)	V <sub>F</sub>	400	mV	I <sub>F</sub> =1mA
		560	mv	I <sub>F</sub> =10mA
		1	v	I <sub>F</sub> =40mA
Reverse current(Fig.2 ;note1)	I <sub>R</sub>	1	μA	V <sub>R</sub> =30V
		10	μA	V <sub>R</sub> =40V
Diode capacitance(Fig.4)	C <sub>d</sub>	5	pF	f=1MHz;V <sub>R</sub> =0

Note:

1. Pulse test:t
- <sub>p</sub>
- =300μs;δ=0.02.

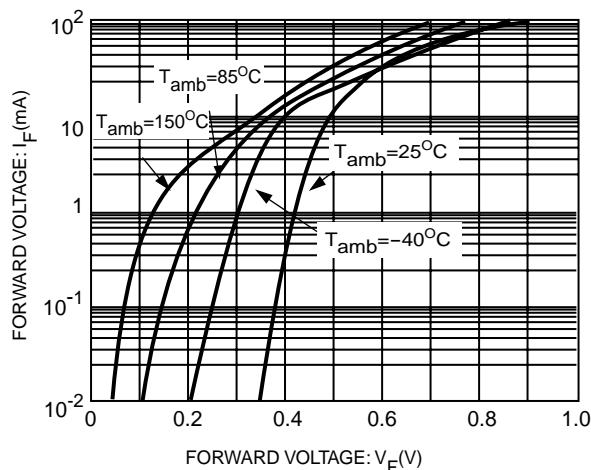
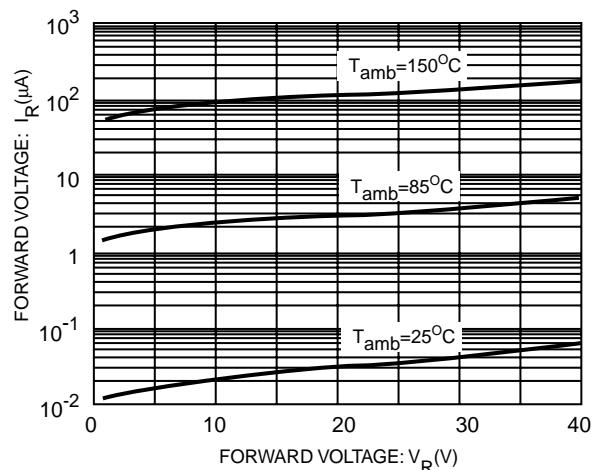
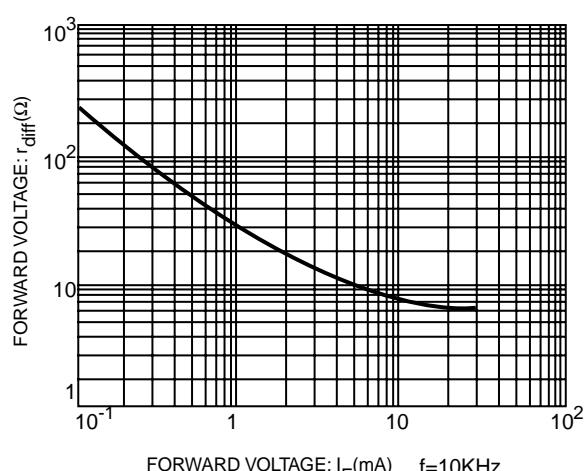
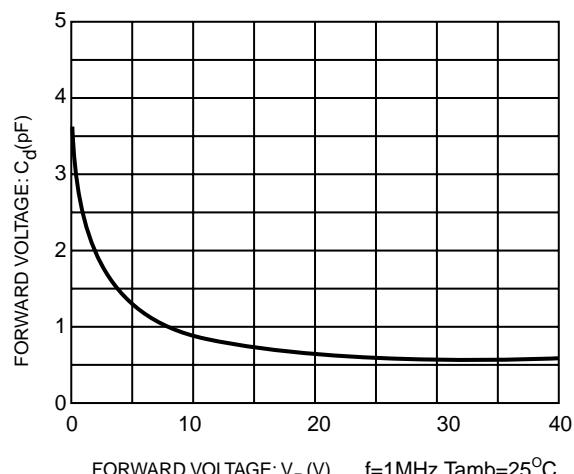
**THERMAL CHARACTERISTICS**

PARAMETER	SYMBOL	VALUE	UNIT	CONDITIONS
Thermal resistance from junction to ambient	R <sub>th j-a</sub>	500	k/w	note1

Note

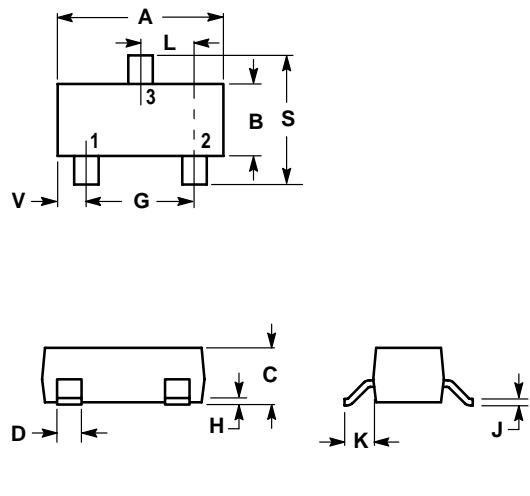
1. Refer to SOT23 or SOT143B standard mounting conditions.

**LBAS40 Series**

 Electrical characteristic curves( $T_A = 25^\circ\text{C}$ )

**Fig.1 Forward current as a function of forward voltage; typical values.**

**Fig.2 Reverse current as a function of reverse voltage; typical values.**

**Fig.3 Differential forward resistance as a function of forward current; typical values.**

**Fig.4 Diode capacitance as a function of reverse voltage; typical values.**

**LBAS40 Series**
**SOT-23**
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

